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A new structural model for the Si(331)-(12×1) reconstruction

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A new structural model for the Si(331)-(12×1) reconstruction is proposed. Based on scanning tunneling microscopy images of unprecedented resolution, low-energy electron diffraction data, and first-principles total-energy calculations, we demonstrate that the reconstructed Si(331) surface shares the same elementary building blocks as the Si(110)-(16×2) surface, establishing the pentamer as a universal building block for complex silicon surface reconstructions.

The study of semiconductor surface reconstructions has been an area of active research for many years and has gained tremendous importance with the advent of low-dimensional heteroepitaxial semiconductor nanostructures such as quantum dots and quantum wires [1]. The creation of a surface results in broken bonds, called dangling bonds. Dangling bonds are energetically unfavorable causing surface atoms to rearrange or reconstruct. This often results in highly complex atomic structures, whose determination remains a formidable challenge and requires the complementary role of different experimental and theoretical methods.

In order to lower the surface energy, silicon surfaces adopt a variety of strategies allowing to reduce the number of dangling bonds. Despite the large number of known surface reconstructions, one frequently encounters common elementary structural building blocks [2, 3]. Identifying these building blocks is important not only for a better understanding of these surfaces, but also serves as a guide for the elaboration of new structural models.

Two of the most important strategies, encountered for instance on Si(100) [4] and Si(111) [5], are respectively the formation of dimers, where two surface atoms pair up to eliminate their dangling bonds, and the appearance of adatoms, which bond to three surface atoms thus saturating three dangling bonds. An important step towards the understanding of high-index group IV surfaces with a surface normal in between the (111) and (100) direction was the introduction of an additional reconstruction element by Dabrowski *et al.* [6]. They proposed a six-fold coordinated surface self-interstitial which is captured by a conglomerate of surface atoms [7, 8]. This concept was subsequently adapted by An [9] and theoretically analyzed by Stekolnikov [10, 11] to explain the pairs of pentagons observed in scanning tunneling microscopy (STM) images of the reconstructed Si(110) surface.

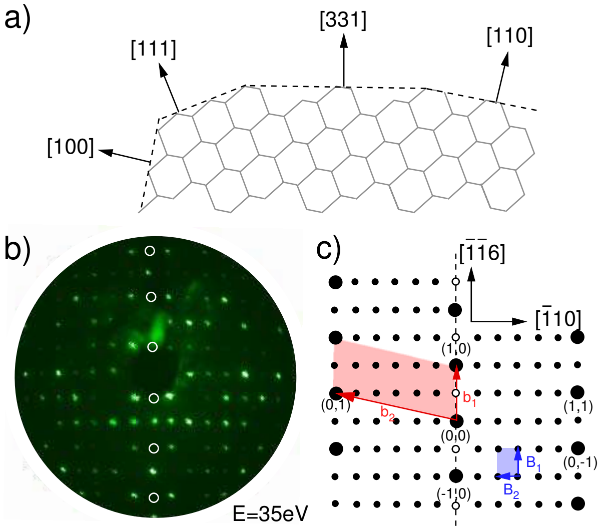

FIG. 1: (Color online) a) Side cutaway showing the crystal lattice of silicon in the ($\bar{1}$10) plane. The dashed line follows the bulk-terminated surface for several important orientations. b) Experimental LEED pattern at 35 eV beam energy. The positions of missing spots are indicated by the white circles. c) Sketch of the LEED pattern with (1×1) (red) and (12×1) (blue) reciprocal unit cells and spot labels (black). The bulk directions are also given. The positions of the missing spots are indicated by empty black circles. The orientation of the glide plane is indicated by a dashed line.

In this letter we focus on the atomic structure of the Si(331)-(12×1) reconstruction. We present high-resolution STM images resolving for the first time rows of pentagons very similar to the ones observed on Si(110)-(16×2). Si(331), whose surface normal is located 22.0^o away from the (111) direction towards (110) (see Fig. 1a)), is an important surface, since it is the only confirmed planar silicon surface with a stable reconstruction located between (111) and (110). Since the discovery of the Si(331)-(12×1) reconstruction more than 17 years ago [12] several structural models containing dimers and adatoms have been proposed [13, 14]. However, none of these models is able to explain the pentagons observed in our STM images. Combining the complementary strength of STM, low-energy electron diffraction (LEED), and first-principles total-energy calculations, we derive a new structural model containing surface self-

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interstitials as basic building blocks.

Sample preparation and experiments were carried out in a ultra-high vacuum chamber with a residual gas pressure below 3×10^{-11} mbar equipped with an Omicron LT-STM and Omicron Spectaleed LEED/Auger optics. Boron doped Si(331) samples from CrysTec with a resistivity of 0.1-30 Ω cm were slowly degassed by direct current heating up to 1060^oC while keeping the pressure below 5×10^{-10} mbar, followed by subsequent cleaning via repeated flashing to 1260^oC and slow cooling across the (1×1) to (12×1) phase transition at 810^oC [12]. This procedure gives an almost perfectly ordered surface with a very low number of defects. Special care was taken in order to avoid Ni contamination. STM measurements were performed at 77 K using etched W tips.

The theoretical results are based on first-principles calculations performed with ABINIT [15]. This code employs a density-functional theory scheme within a plane-wave expansion, where we have used norm-conserving pseudopotentials and the local-density approximation for the exchange-correlation potential. ABINIT has already been successfully applied to describe the Si(113) surface [16]. The present (331) surface has been studied using a slab supercell containing 240 bulk silicon atoms, plus a variable number of surface atoms (depending on the reconstruction). The bottom surface was passivated with 36 hydrogen atoms and adjacent slabs are separated by 9.4 Å of vacuum. Convergence required a kinetic-energy cutoff of 218 eV and a single (nonzero) k-point in the Brillouin zone, yielding an accuracy of the calculated forces of 0.077 eV/Å. In order to accelerate the convergence of the self-consistent cycle we introduced a metallic broadening of 0.054 eV.

Figure 1b) presents a normal incidence LEED pattern of the Si(331)-(12×1) reconstruction. The corresponding sketch containing reciprocal lattice vectors and spot labels (h, k) is shown in Fig. 1c). The bulk-terminated surface is chosen as the reference for indexing. The reciprocal unit cell vectors $\mathbf{B}_1$ and $\mathbf{B}_2$ of the reconstructed surface can be expressed using the reciprocal unit cell vectors $\mathbf{b}_1$ and $\mathbf{b}_2$ of the bulk-terminated (331) surface

$$\begin{pmatrix} \mathbf{b_1} \\ \mathbf{b_2} \end{pmatrix} = \begin{pmatrix} 2 & 0 \\ 1 & 6 \end{pmatrix} \begin{pmatrix} \mathbf{B_1} \\ \mathbf{B_2} \end{pmatrix}.$$

However, since in general we find 11 satellite diffraction spots in between the integer spots along the $[\bar{1}10]$ direction, the reconstruction is conventionally called the (12×1) reconstruction in the literature.

The spot intensities in the LEED pattern in Fig. 1b) exhibit a mirror symmetry along the $[\bar{1}\bar{1}6]$ direction. Furthermore, a careful analysis of the LEED spot intensities as a function of energy (not shown) reveals that systematically *all* half-order spots $(\pm nh/2, 0)$, n being an odd integer, are missing for *all* beam energies (see empty circles in Fig. 1b) and c). Although spot intensities vary as a function of energy and even vanish at some energies due to diffraction effects, the $(\pm nh/2, 0)$ spots exhibit no intensity at *all* beam energies. Such missing spots indicate the existence of a glide plane along $[\bar{1}\bar{1}6]$ in real space [17, 18]. This glide plane also implies the mirror symmetry observed for the LEED intensities in reciprocal space [19]. Thus LEED firmly establishes the presence of a glide plane in the structure.

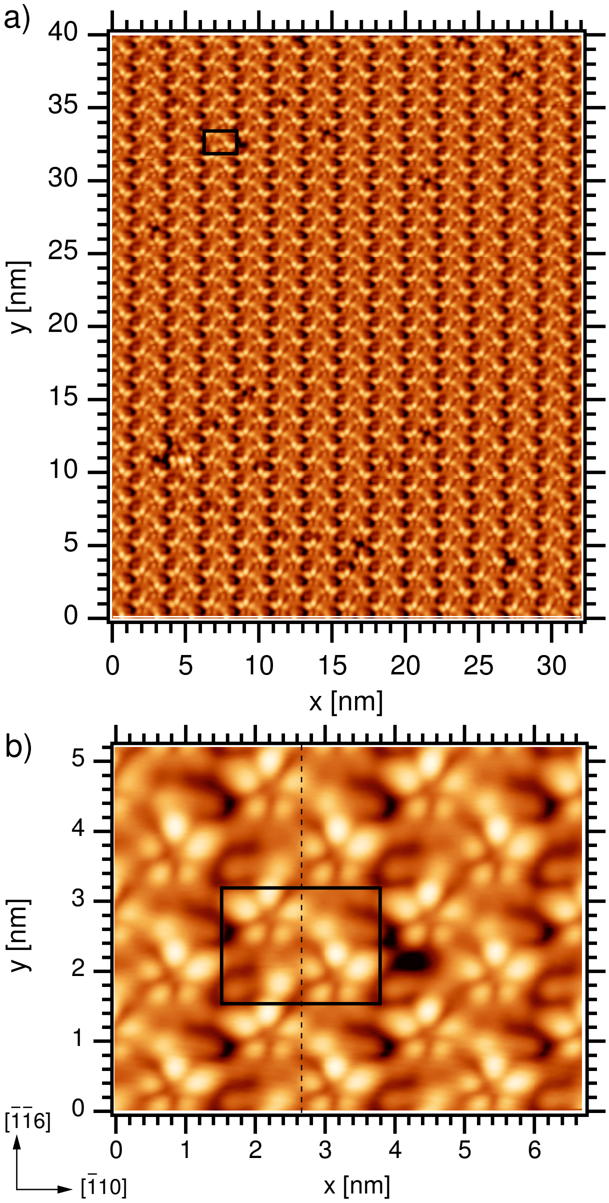

FIG. 2: (Color online) a) Large scale STM topography of the annealed Si(331) surface. b) High-resolution image with unit cell (full line) and the glide plane (dashed line) indicated. Bias voltage 2.0 V, set-point current 0.06 nA.

We now turn to our STM data. The large scale topography image presented in Fig. 2a) shows the high quality of the surface. Besides the perfect long range order only a few local defects are present on the surface. As already observed by several other groups [14, 20, 21, 22, 23, 24], the Si(331)-(12×1) reconstruction consists of similar mounds arranged into zigzag chains running along the $[\bar{1}\bar{1}6]$ direction separated by trenches. Focusing now on the high-resolution image in Fig. 2b) we see that each of the mounds consists of five protrusions forming a pentagon. A further protrusion may be identified linking two successive pentagons within the same chain. Pentagons with the same dimensions were already observed on Ge(110)-c(8×10) [25, 26] as well as on Ge(110)-(16×2) [25] and on Si(110)-(16×2) [9]. To our knowledge this is *the first observation of such pentagons on a surface away from the (110) orientation*, indicating their high stability and confirming their fundamental role as an elementary building block in semiconductor surface reconstructions.

Inspired by structural elements encountered on reconstructed Si(113) and Ge(113) surfaces [6, 7], An *et al.* [9] have proposed an adatom-tetramer-interstitial (ATI) model for the pentagons observed on the (110) surfaces. Its stability has subsequently been tested theoretically by means of first-principles total-energy calculations [10, 11].

In the following, we develop a coherent structural model for the Si(331)-(12×1) reconstruction inspired by the ATI model and discuss similarities and differences with the (110) case. In a first step we need to determine the registry of the surface reconstruction with respect to the bulk. This is not a trivial task, so we proceed in two steps. We focus first on the position of the surface reconstruction with respect to the underlying bulk along the $[\bar{1}10]$ direction. Here the occurrence of the glide plane symmetry gives us the clue. Inspection of Fig. 2b) shows that a glide plane is found at the center of the zigzag chain (dashed line) consistent with the observation of missing spots in the LEED pattern. The glide plane found on the surface must also be a glide plane of the bulk, since the space group of the bulk contains all symmetry elements of the surface. A side view of the bulk terminated Si(331) surface is shown in Fig. 3a) with a top view of our model in Fig. 3b). The dashed line represents the glide plane. Fig. 3c) offers a graphical proof for the existence of the glide plane in the bulk. After mirror reflection along the glide plane line, a translation by half the unit vector $-\mathbf{A}_1/2$ is necessary to obtain the original registry.

After determining the registry of the surface reconstruction with respect to the $[\bar{1}10]$ direction we now need to study the registry with respect to the $[\bar{1}\bar{1}6]$ direction. Here we benefit from a comparison with the Si(110) surface shown schematically in Fig. 3e) and f). For a sketch of the complete model for the Si(110)-(16×2) reconstruction including the steps along $[\bar{1}12]$ see Ref. [11]. According to the ATI model for the Si(110) surface, the pentagon seen in STM images consists of four adatoms (a,b,c,d, empty circles) forming the tetramer and one surface atom (e, black dot) belonging to the first atomic layer (see Fig. 3d)). The six-fold coordinated interstitial atom (f, empty circle) is located at the center of the pentagon slightly below the tetramer plane and consequently not directly visible in STM images (see simulated STM images in Ref. [11]). The resulting structural element formed by the tetramer, atom e and f combined is called a pentamer [11].

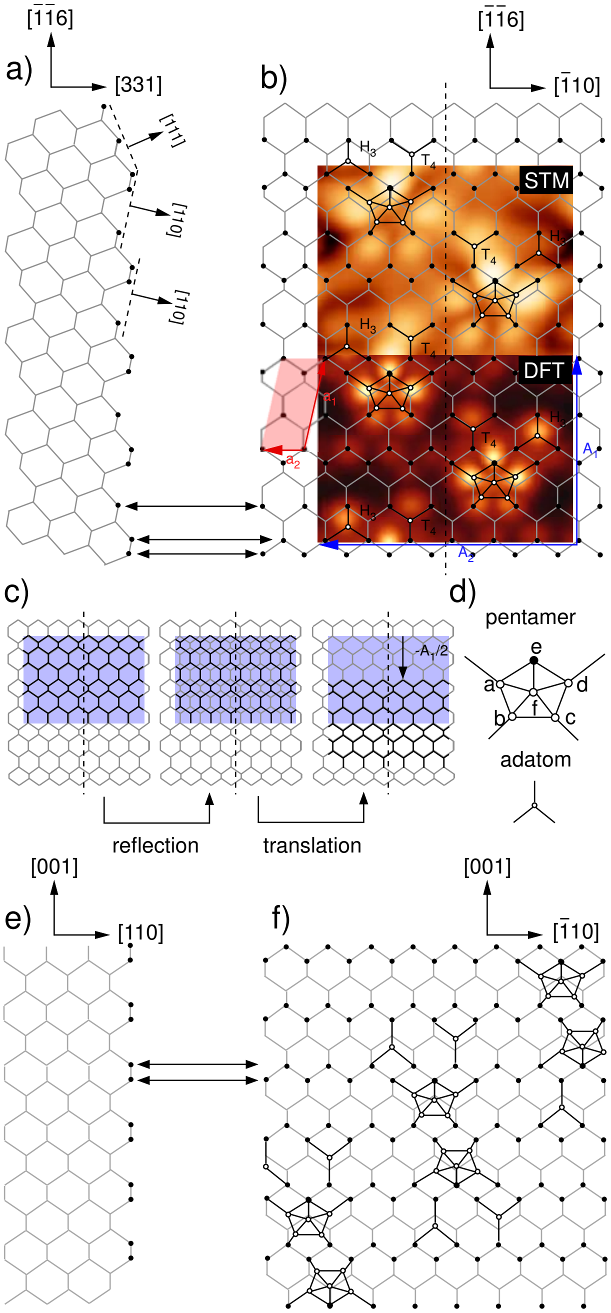

FIG. 3: (Color online) a) Side and b) top view of the Si(331) surface. Black dots indicate the position of dangling bonds, some of which are saturated by pentamers and adatoms (empty circles). The (1×1) (red) and (12×1) (blue) unit cells are shown. For comparison an experimental and a simulated STM image is underlaid. The dashed line represents the glide plane. c) Graphical proof for the existence of the glide plane. d) Sketch of the pentamer and the adatom with atom labels. e) Side and f) top view of the Si(110) surface. (see text)

In order to integrate the pentamer building block into our model we note that the arrangement of dangling bonds on the bulk-truncated surface represented by black dots and marked by the double headed arrows in Fig. 3 differs between the Si(110) and Si(331) surface. Whereas dangling bonds on the Si(110) surface occur in double rows running along [$\bar{1}$10], double rows alternate with single rows of dangling bonds on the bulk-terminated Si(331) surface. For the Si(110) structure, atom e actually belongs to one of these dangling bond double rows. Consequently we also anchor the two pentamers per unit cell required by STM on the double dangling bond row of the bulk-terminated Si(331) surface. It is important to note that anchoring the pentamers in this way provides exactly the same local binding configuration as on the Si(110) surface, since careful comparison of the sideviews in Fig. 3a) and e) reveals that the bulk-truncated Si(331) surface can be viewed as a highly stepped Si(110) surface. The selected position of the pentagons agrees with the position observed in the STM images (see STM image behind the model in Fig. 3b)). Note also that the single dangling bond row of the Si(331) surface is slightly lower-lying than the double dangling bond row, causing an inclination of the pentamer, in agreement with the lower intensity of the lobes associated with adatom b and c in the experimental STM image.

Each pentamer saturates five of the surrounding dangling bonds [10]. By introducing two pentamers per Si(331)-(12×1) unit cell, the number of dangling bonds has been reduced from 36 to 26. Some of the remaining dangling bonds are saturated by simple adatoms as in the case of the Si(110) surface. In the STM image in Fig. 2b) the additional protrusion linking two successive pentamers indicates the location of a first adatom, labeled T_4 in Fig. 3b) in analogy with the convention used to label this adatom position on the (111) surface. The local binding configuration for this T_4 adatom on the Si(331) surface is exactly the same as on the (111) surface, where adatoms are common structural building blocks. A further adatom labeled H_3 saturates three more dangling bonds.

Introducing two T_4 and two H_3 adatoms per unit cell into our structural model further reduces the number of dangling bonds from 26 to 14. For Si(110) Stekolnikov *et al.* [11] have noted that it is energetically more favorable to leave some surface atoms, so called rest atoms, unsaturated than to introduce the maximum number of adatoms into the model, since this allows a further reduction of the surface energy by electron transfer from the adatom to the rest atom in analogy with the Si(111)-(7×7) case [27].

We have explicitly verified the stability of the reconstruction containing two T_4 and two H_3 adatoms by means of first-principles calculations testing various alternative adatom configurations, among which the present one yields the highest stability (details on the theoretical investigations will be published elsewhere [28]). In Fig. 3b) we also show a simulated STM image based on relaxed coordinates of our structural model, obtained by integrating the local state density over a 2.0 eV energy window corresponding to the experimental STM bias voltage. The DFT image is in excellent agreement with the experimental STM image. The theoretical image reproduces well the strong intensity of the lobes associated with atoms a, e and d and the weaker intensity associated with atoms b and c of the pentamer. In general the topographical features in the simulated image show better resolution and less diffuse character than the corresponding features observed in STM, since the simulation neglects any role of the tip structure in degrading image resolution [29]. In the experimental as well as in the simulated image, individual pentagons do not exhibit a mirror symmetry along the [$\bar{1}\bar{1}$6] direction indicating a distortion of the pentagon which allows to reduce internal strain. Furthermore the T_4 and H_3 adatoms in the simulated image are seen as a marked protrusion in agreement with experiment.

It is interesting to note that on the Si(110) surfaces, pentamers always occur in twin pairs rotated by 180^o with respect to each other, whereas on Si(331) all pentamers point into the same direction and are further apart from each other. Comparing the transition temperature of 810^oC [12] for Si(331)-(12×1) with 730^oC [30] for Si(110)-(16×2), it appears that Si(331) is the more favorable surface for pentamer formation (for comparison the transition temperature of 870^oC [31] for the Si(111)-(7×7) reconstruction is slightly higher). Further detailed total-energy calculations are required to quantify the trade-off between surface dangling bond reduction and induced surface stress and to compare the differences in the bonding configuration between the Si(331) and the Si(110) surface.

In summary, by combining STM, LEED, first-principles calculations and by comparing similarities and differences between the Si(331)-(12×1) and Si(110)-(16×2) reconstructions, we have derived a complete structural model for the Si(331) surface containing the pentamer as an essential ingredient. Thus besides adatoms, dimers and tetramers, pentamers emerge as a universal building blocks for silicon surface reconstructions.

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